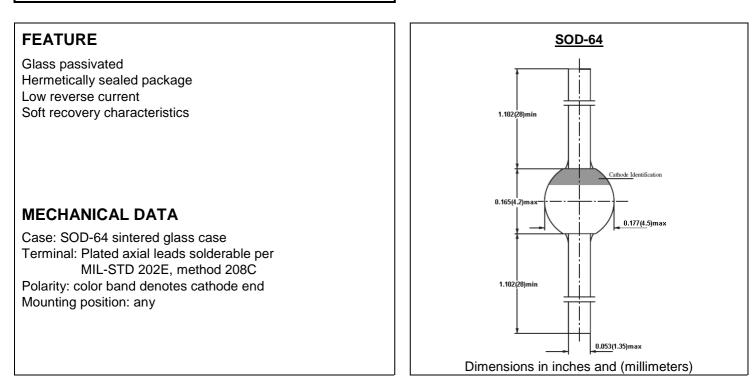
## BYT56M

## SINTERED GLASS JUNCTION FAST AVALANCHE RECTIFIER

VOLTAGE: 1000V





CURRENT: 3.0A

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	BYT56M	units
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	700	V
Maximum DC blocking Voltage	V <sub>DC</sub>	1000	V
Maximum Average Forward Rectified Current 3/8"lead length at I =10mm	I <sub>FAV</sub>	3.0	А
Peak Forward Surge Current at tp=10ms,half sinewave	I <sub>FSM</sub>	80	А
Maximum Forward Voltage at rated Forward Current at IF=3.0A	V <sub>F</sub>	1.4	V
Non-repetitive peak reverse avalanche energy at $I_{BR(R)}=0.4A$	E <sub>RSM</sub>	10	mJ
Maximum DC Reverse CurrentTa = $25^{\circ}C$ at rated DC blocking voltageTa = $150^{\circ}C$	I <sub>R</sub>	5.0 150.0	μA μA
Maximum Reverse Recovery Time (Note 1)	Trr	100	nS
Typical Thermal Resistance (Note 2)	Rth(ja)	70	°C /M
Storage and Operating Junction Temperature	Tstg, Tj	-55 to +175	°C

Note:

1. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A

2. on PC board with spacing 25 mm

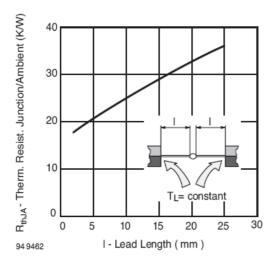


Figure 1. Max. Thermal Resistance vs. Lead Length

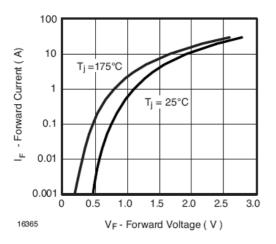


Figure 2. Forward Current vs. Forward Voltage

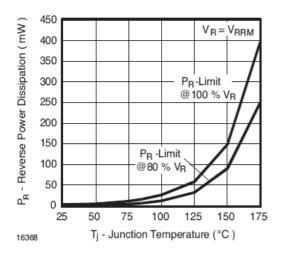


Figure 5. Max. Reverse Power Dissipation vs. Junction Temperature

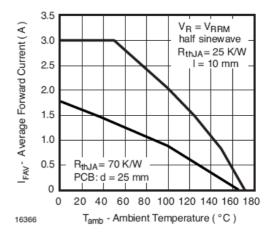


Figure 3. Max. Average Forward Current vs. Ambient Temperature

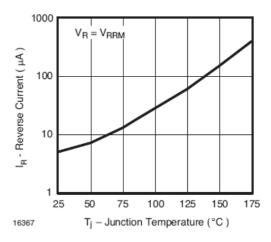


Figure 4. Reverse Current vs. Junction Temperature

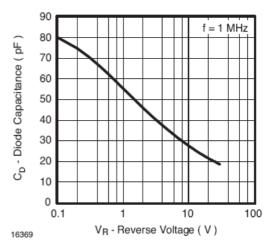


Figure 6. Diode Capacitance vs. Reverse Voltage

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